

Features

- 14 dB Gain at 2000 MHz
- 27 dBm P1dB at 2000 MHz
- 42 dBm OIP3 at 2000 MHz
- ACLR @ WCDMA 4FA : -51 dBc @ Pout =13 dBm, +/- 5MHz offset
- MTTF > 100 Years
- Single Supply

Description

The ASX415, a power amplifier MMIC, has a high linearity, high gain, and high efficiency over a wide range of frequency, being suitable for use in both receiver and transmitter of telecommunication systems up to 4 GHz. The amplifier is available in an SOT-89 package and passes through the stringent DC, RF, and reliability tests.



Package Style: SOT-89

Typical Performance

Parameters	Units	Typical				
		900	2000	2000	2000	2600
Frequency	MHz	900	2000	2000	2000	2600
Gain	dB	20	14.5	14.3	14	11.5
S11	dB	-14	-7	-7	-7	-7
S22	dB	-13	-11	-11	-11	-10
Output IP3 ¹⁾	dBm	42.5	46	42	40	37
Noise Figure	dB	4.2	5.6	4.6	4.1	4.2
Output P1dB	dBm	29	29	27	26.5	29
Current	mA	155	185	155	123	155
Device Voltage	V	5	5.3	5	4.75	5

1) OIP3 is measured with two tones at an output power of +8 dBm/tone @ 5.3V & +6 dBm/tone @ 5V & +4 dBm/tone @ 4.75V separated by 1 MHz.

Product Specifications

Parameters	Units	Min	Typ	Max
Testing Frequency	MHz		2000	
Gain	dB	13.5	14.3	
S11	dB		-9	
S22	dB		-11	
Output IP3	dBm	40	42	
Noise Figure	dB		4.6	
Output P1dB	dBm	26.5	27	
Current	mA	140	155	170
Device Voltage	V		5	

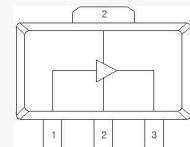
Absolute Maximum Ratings

Parameters	Rating
Operating Case Temperature	-40 to +85°C
Storage Temperature	-40 to +150°C
Device Voltage	+6 V
Operating Junction Temperature	+150°C
Input RF Power (Continuous)	22 dBm

Application Circuit

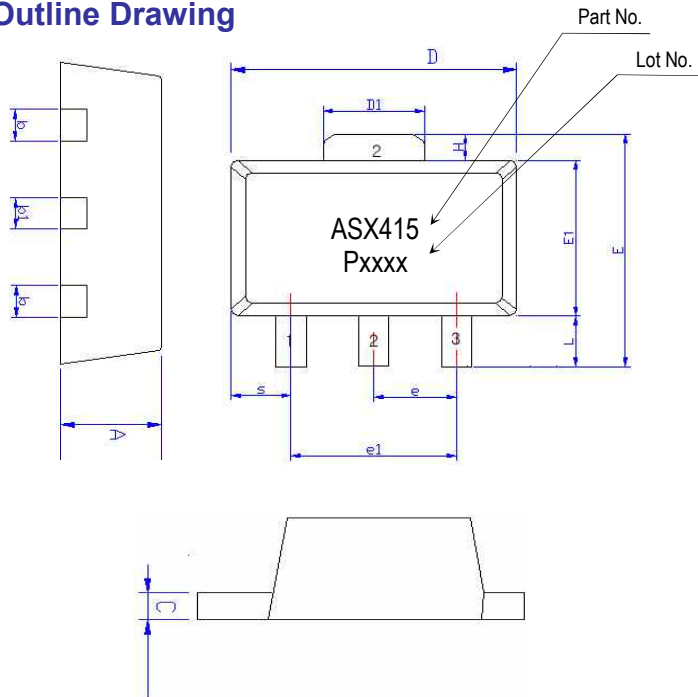
- 433 ~ 444MHz
- CDMA
- Satellite Phone
- WCDMA
- WiMAX
- LTE (2300 ~ 2700MHz)

Pin Configuration



Pin No.	Function
1	RF IN
2	GND
3	RF OUT / Bias

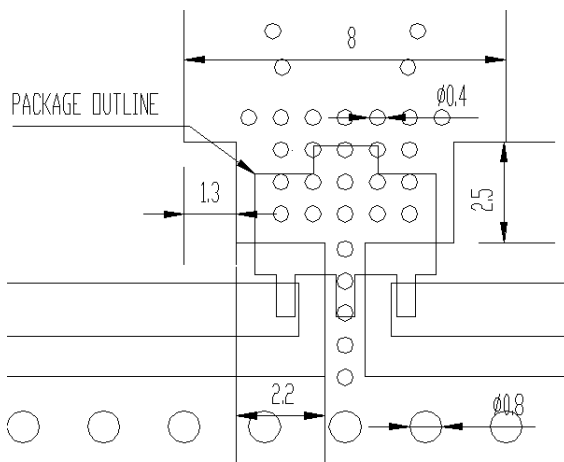
Outline Drawing



Symbols	Dimensions (In mm)		
	MIN	NOM	MAX
A	1.40	1.50	1.60
L	0.89	1.04	1.20
b	0.36	0.42	0.48
b1	0.41	0.47	0.53
C	0.38	0.40	0.43
D	4.40	4.50	4.60
D1	1.40	1.60	1.75
E	3.64	---	4.25
E1	2.40	2.50	2.60
e1	2.90	3.00	3.10
H	0.35	0.40	0.45
S	0.65	0.75	0.85
e	1.40	1.50	1.60

Pin No.	Function
1	RF IN
2	GND
3	RF OUT / Bias

Mounting Recommendation (in mm)



- Note:**
1. The number and size of ground via holes in a circuit board is critical for thermal and RF grounding considerations.
 2. We recommend that the ground via holes be placed on the bottom of the lead pin 2 and exposed pad of the device for better RF and thermal performance, as shown in the drawing at the left side.

Ordering Information

Part Number	Description
-------------	-------------

APPLICATION CIRCUIT

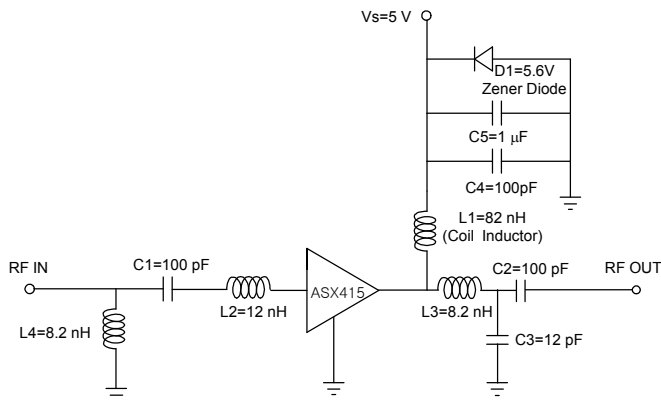
433~444

+5 V

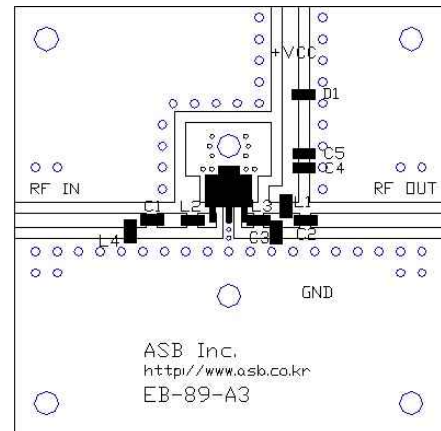
Frequency (MHz)	433	444
Magnitude S21 (dB)	22	22
Magnitude S11 (dB)	-18	-18
Magnitude S22 (dB)	-16	-15
Output P1dB (dBm)	28	28
Output IP3 ¹⁾ (dBm)	35	37
Noise Figure (dB)	6.5	6
Device Voltage (V)	5	5
Current (mA)	155	155

1) OIP3 is measured with two tones at an output power of +5 dBm/tone separated by 1MHz.

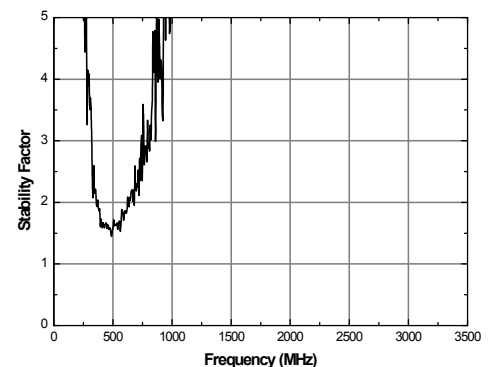
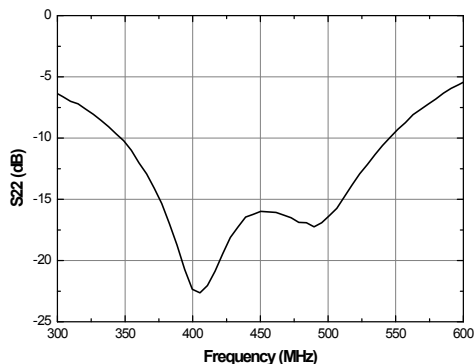
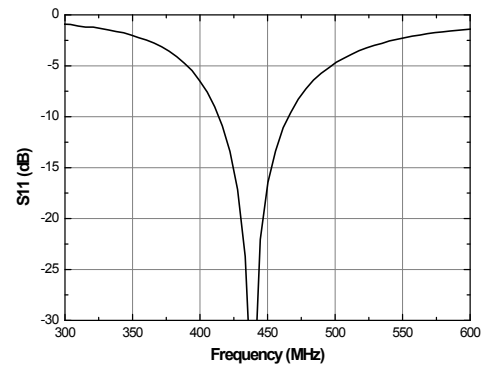
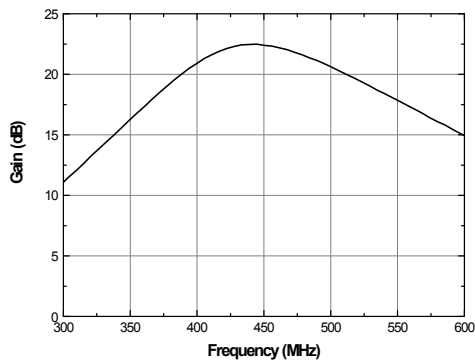
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



APPLICATION CIRCUIT

CDMA Rx

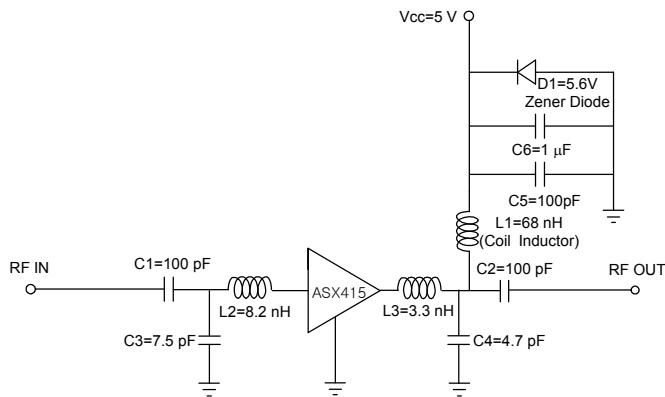
824 ~ 849

+5.3 V / +5 V / +4.75 V

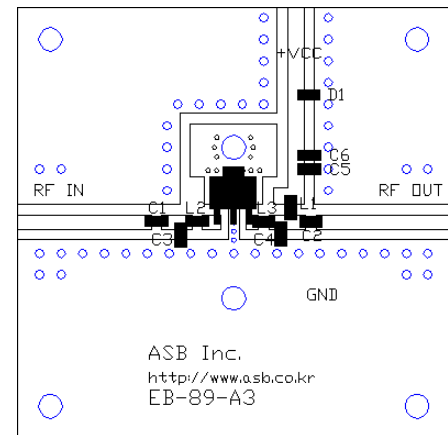
Frequency (MHz)	824~849		
Magnitude S21 (dB)	20.3	20	19.8
Magnitude S11 (dB)	-15	-15	-14
Magnitude S22 (dB)	-12	-12	-12
Output P1dB (dBm)	28.5	28.5	28
Output IP3 ¹⁾ (dBm)	45	41	35
Noise Figure (dB)	5.2	4.4	4.2
Device Voltage (V)	5.3	5	4.75
Current (mA)	185	155	123

1) OIP3 is measured with two tones at an output power of +7 dBm/tone @ 5.3V & +6 dBm/tone @ 5V & +4 dBm/tone @ 4.75V separated by 1MHz.

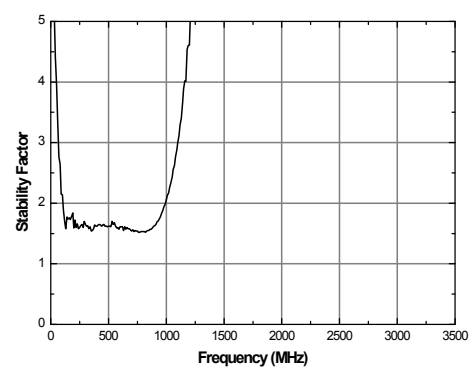
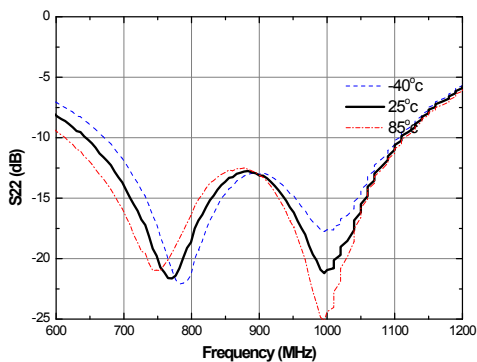
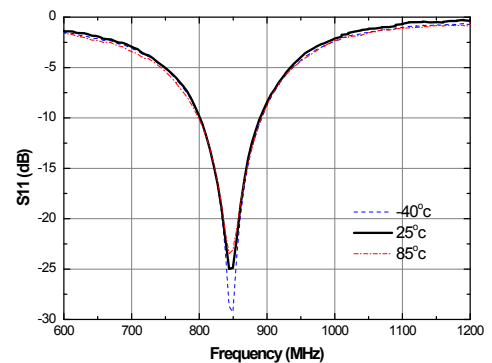
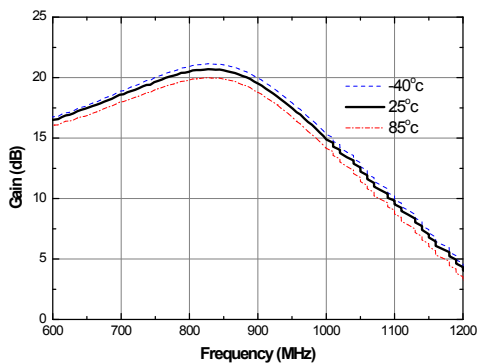
Schematic



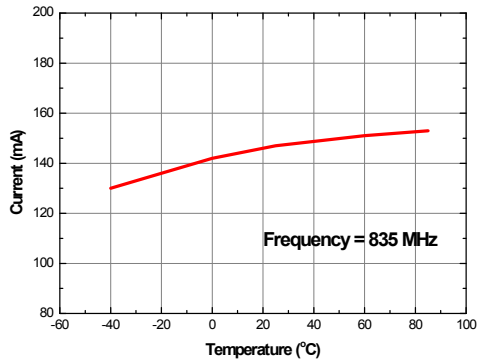
Board Layout (FR4, 40x40 mm², 0.8T)



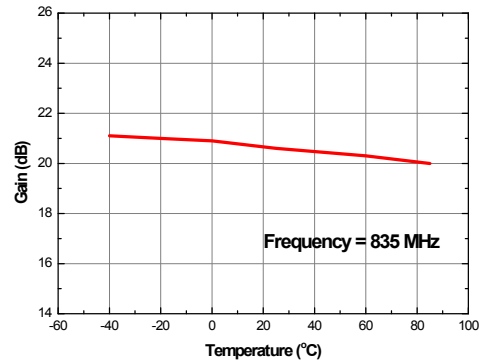
S-parameters & K-factor



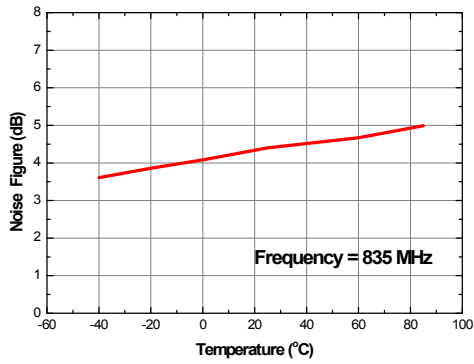
Current vs. Temperature



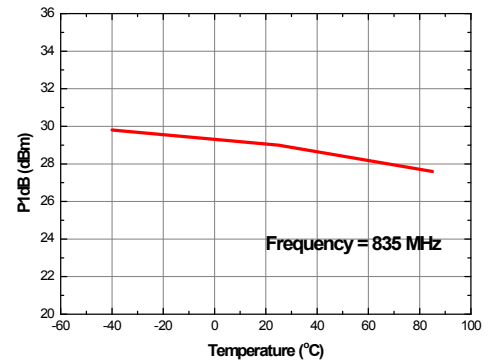
Gain vs. Temperature



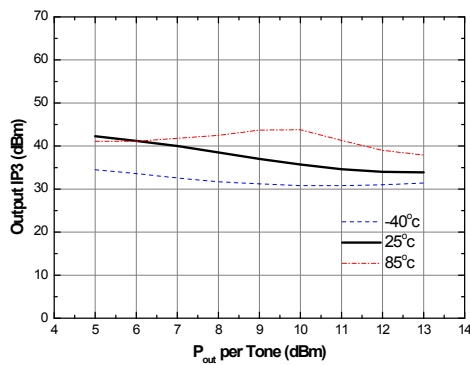
Noise Figure vs. Temperature



P1dB vs. Temperature



Output IP3 vs. Tone Power (Frequency = 835 MHz)



APPLICATION CIRCUIT

CDMA Tx

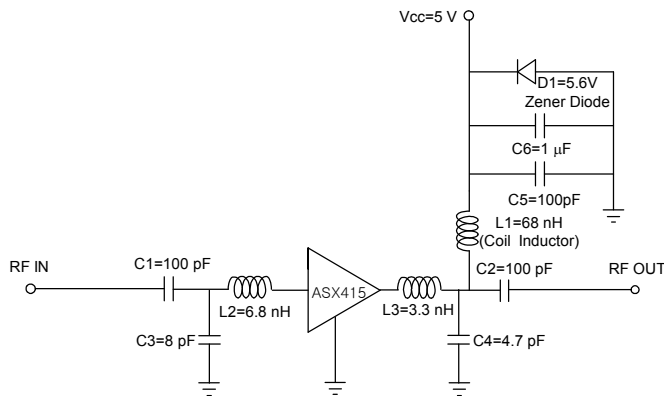
869 ~ 894

+5.3 V / +5 V / +4.75 V

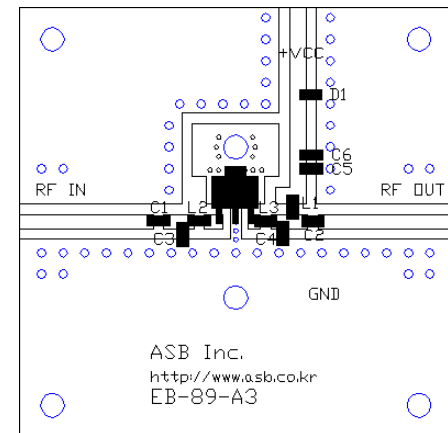
Frequency (MHz)	869~894		
Magnitude S21 (dB)	20.1	20	19.7
Magnitude S11 (dB)	-14	-14	-12
Magnitude S22 (dB)	-13	-13	-13
Output P1dB (dBm)	29	29	27.5
Output IP3 ¹⁾ (dBm)	45	42.5	39
Noise Figure (dB)	5.2	4.2	4.2
Device Voltage (V)	5.3	5	4.75
Current (mA)	185	155	123

1) OIP3 is measured with two tones at an output power of +5 dBm/tone @ 5.3V & +6 dBm/tone @ 5V & +10 dBm/tone @ 4.75V separated by 1MHz.

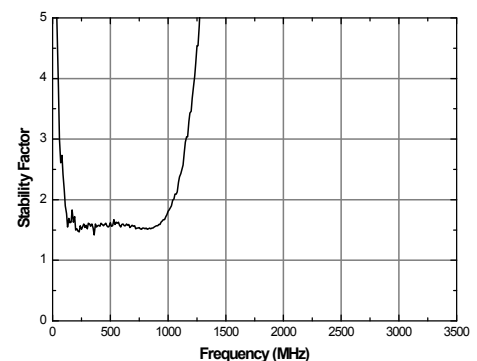
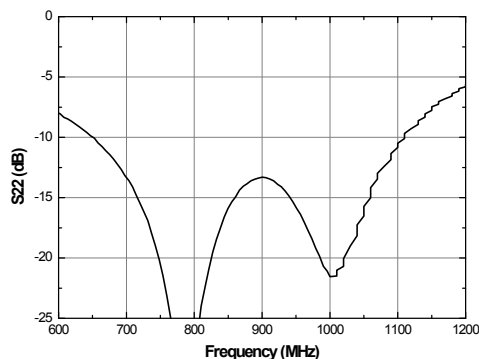
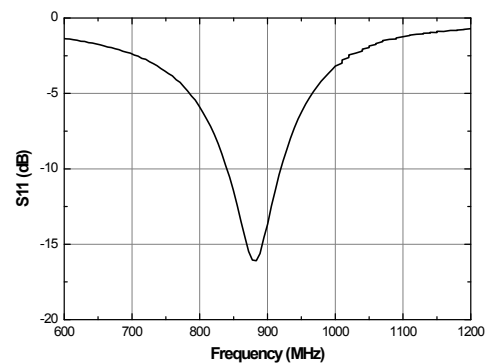
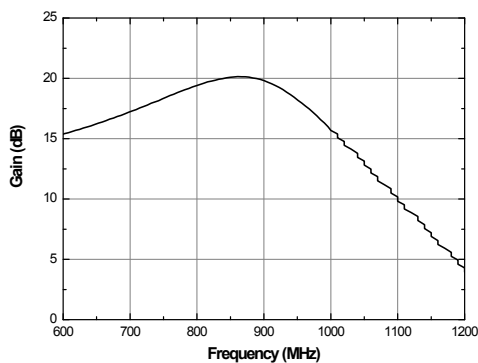
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



APPLICATION CIRCUIT

Satellite Phone

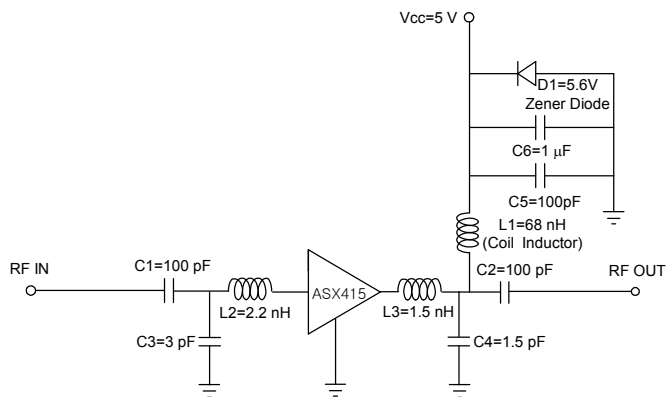
1626 ~1661

+5 V

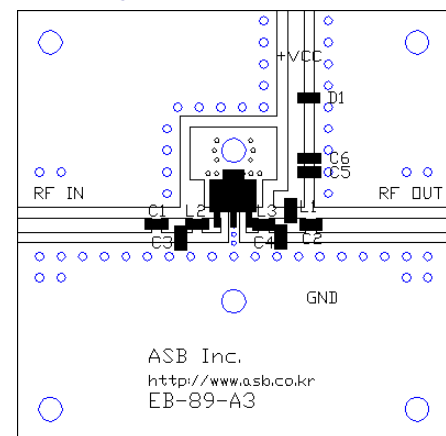
Frequency (MHz)	1626~1661
Magnitude S21 (dB)	16.5
Magnitude S11 (dB)	-14
Magnitude S22 (dB)	-18
Output P1dB (dBm)	29
Output IP3 ¹⁾ (dBm)	37.5
Noise Figure (dB)	3.8
Device Voltage (V)	5
Current (mA)	155

1) OIP3 is measured with two tones at an output power of +6 dBm/tone separated by 1MHz.

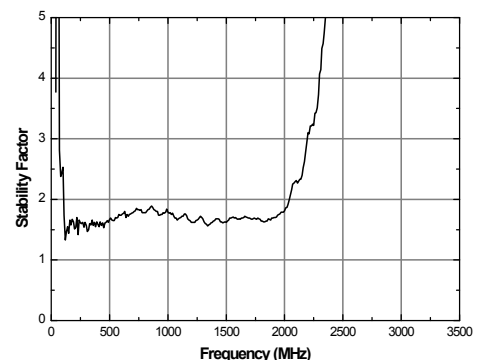
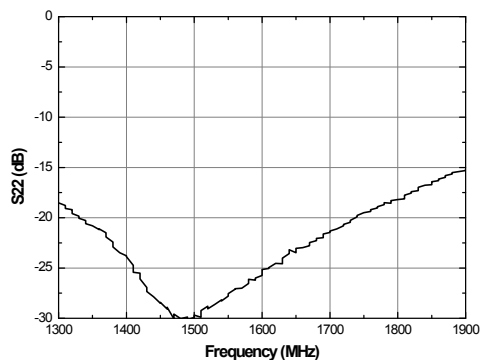
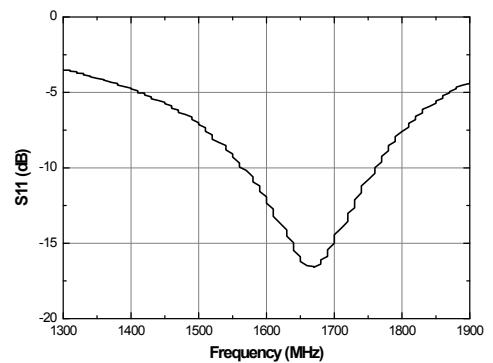
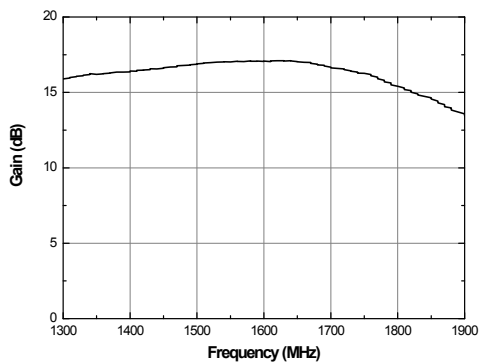
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



APPLICATION CIRCUIT

WCDMA Rx

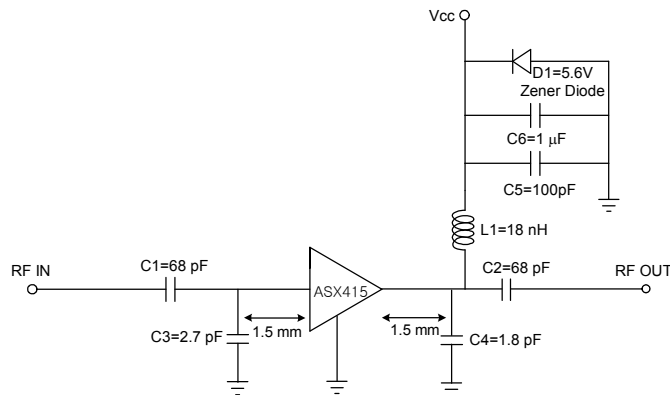
1920 ~ 1980

+5.3 V / +5 V / +4.75 V

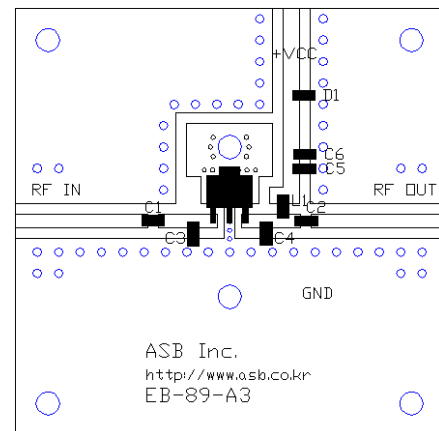
Frequency (MHz)	1920~1980		
Magnitude S21 (dB)	14.5	14.3	14
Magnitude S11 (dB)	-7	-7	-7
Magnitude S22 (dB)	-11	-11	-11
Output P1dB (dBm)	29	27	26.5
Output IP3 ¹⁾ (dBm)	46	42	40
Noise Figure (dB)	5.6	4.6	4.1
Device Voltage (V)	5.3	5	4.75
Current (mA)	185	155	123

1) OIP3 is measured with two tones at an output power of +8 dBm/tone @ 5.3V & +6 dBm/tone @ 5V & +4 dBm/tone @ 4.75V separated by 1MHz.

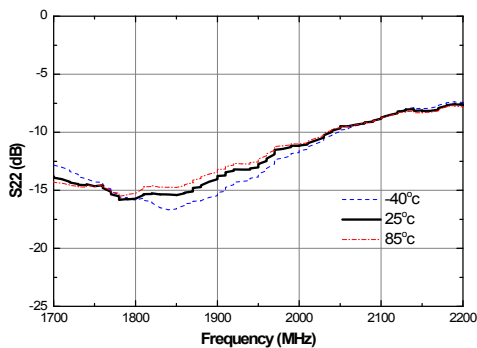
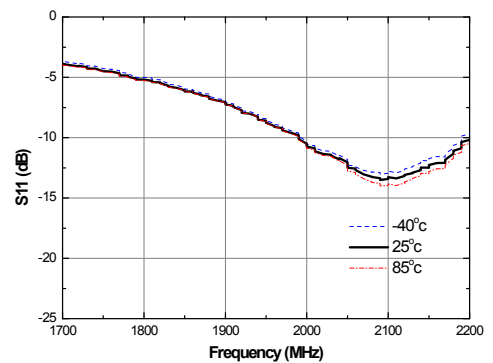
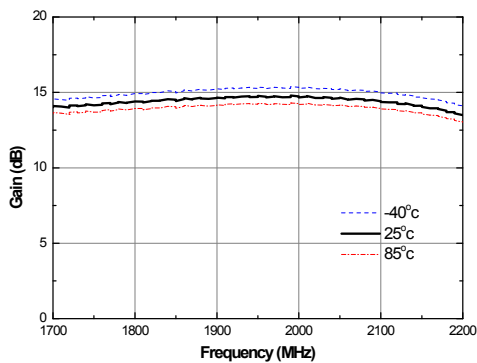
Schematic



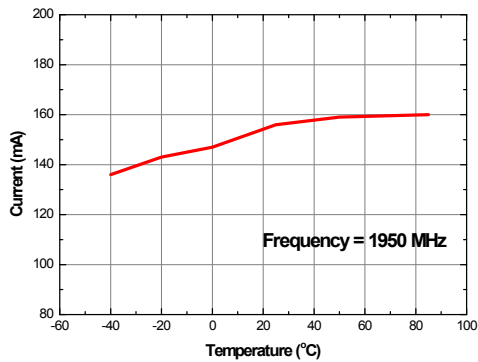
Board Layout (FR4, 40x40 mm², 0.8T)



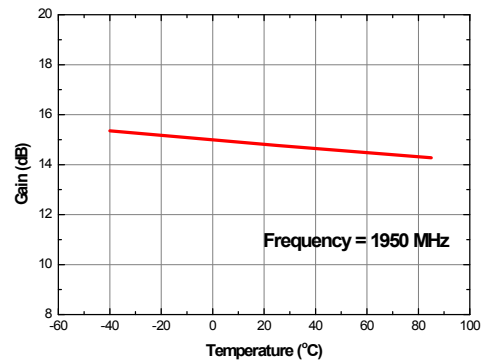
S-parameters & K-factor (5V)



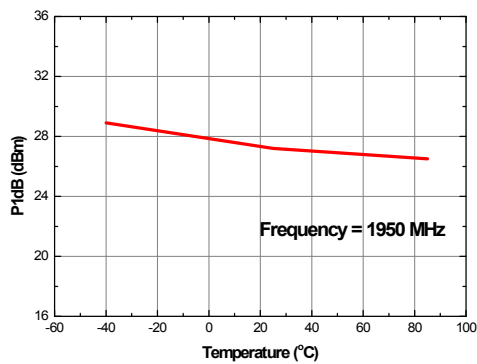
Current vs. Temperature



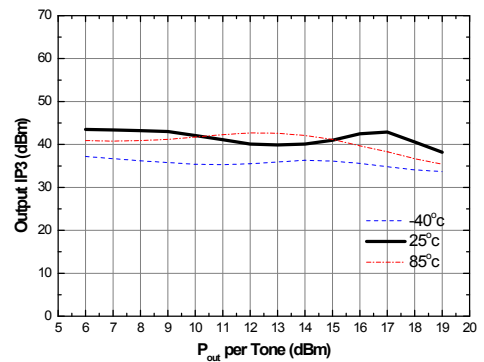
Gain vs. Temperature



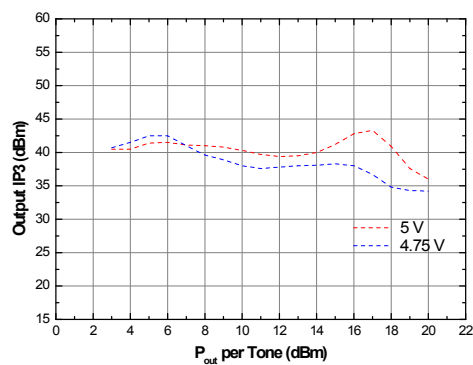
P1dB vs. Temperature



Output IP3 vs. Tone Power (Frequency=1950MHz)

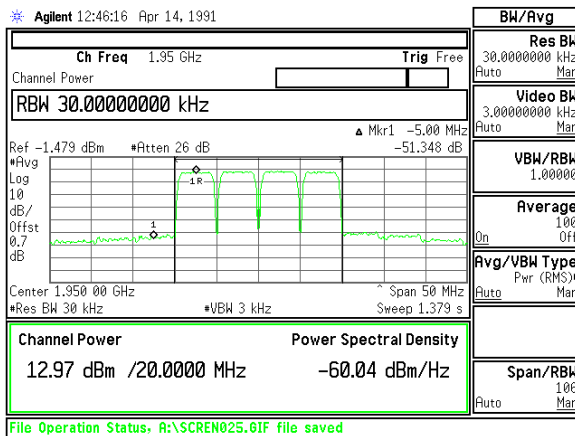


Output IP3 vs. Tone Power (Frequency = 1950 MHz)

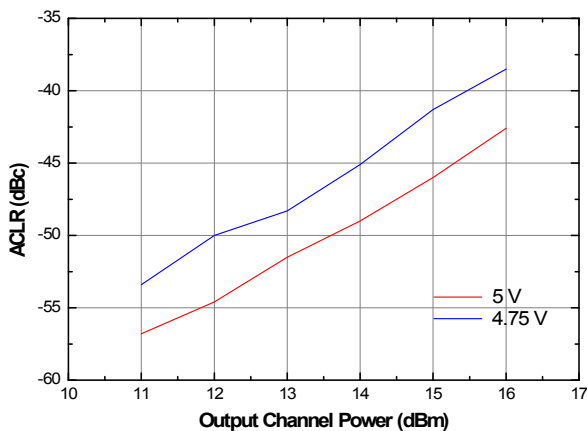
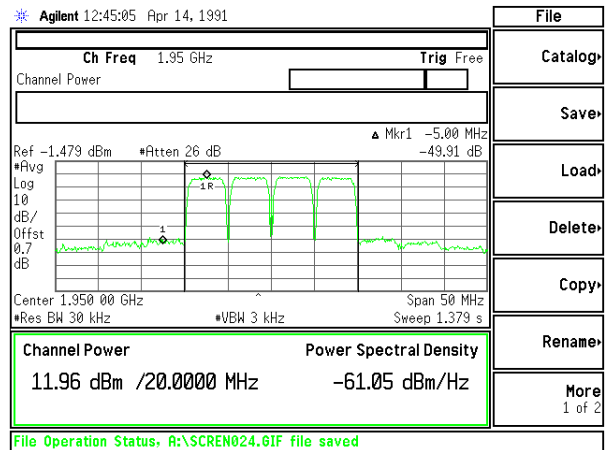


WCDMA ACLR – 4FA

5V / 155mA

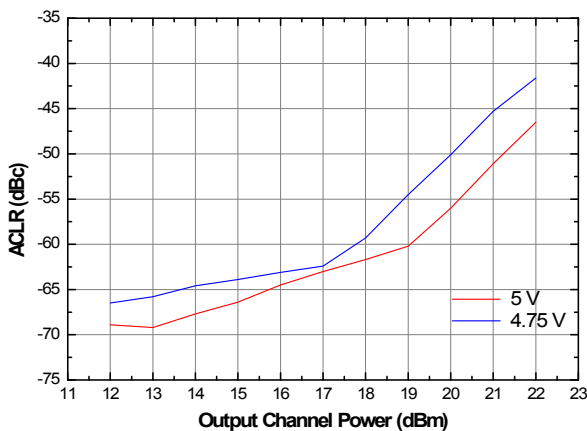


4.75V / 123mA



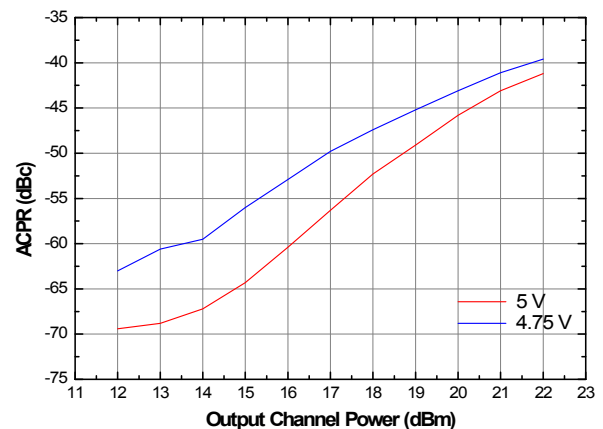
* Test Source : WCDMA 4FA(3GPP 3.4 12-00), Test Model1 w/64 DPCH, PAR=13dB @ 0.01 % probability on CCDF / 1950MHz / 5MHz offset

WCDMA ACLR – 1FA



* Test Source : WCDMA 1FA(3GPP 3.4 12-00), Test Model1 w/64 DPCH, PAR=13dB @ 0.01 % probability on CCDF / 1950MHz / 5MHz offset

CDMA ACPR – 1FA



* Test Source : IS-95, 9ch. Forward 30kHz Meas BW, 1950MHz / 750kHz offset

APPLICATION CIRCUIT

WCDMA Tx

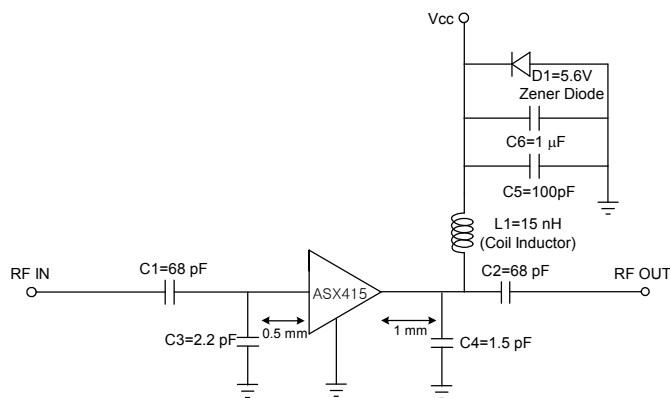
2110 ~ 2170

+5.3 V / +5 V / +4.75 V

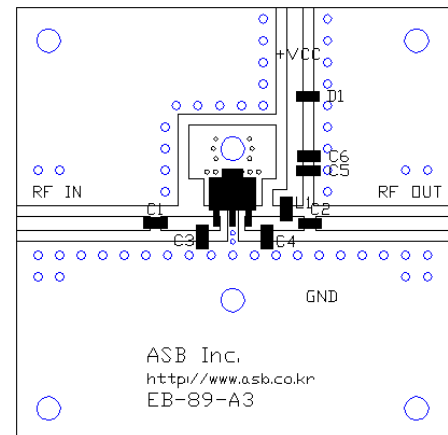
Frequency (MHz)	2110~2170		
Magnitude S21 (dB)	13.2	13	12.8
Magnitude S11 (dB)	-6	-6	-6
Magnitude S22 (dB)	-12	-12	-12
Output P1dB (dBm)	28.5	27.5	27
Output IP3 ¹⁾ (dBm)	46	40.5	39.5
Noise Figure (dB)	6.0	4.9	4.5
Device Voltage (V)	5.3	5	4.75
Current (mA)	185	155	123

1) OIP3 is measured with two tones at an output power of +8 dBm/tone @ 5.3V & +6 dBm/tone @ 5V & +4 dBm/tone @ 4.75V separated by 1MHz.

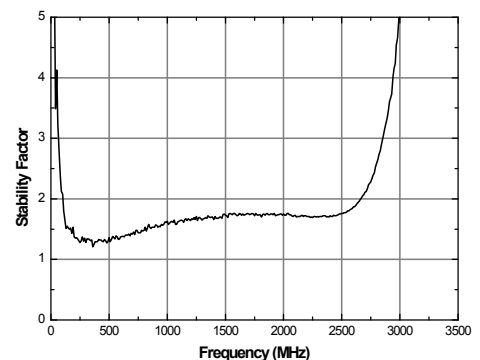
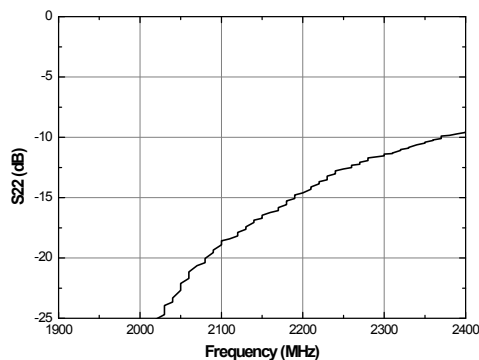
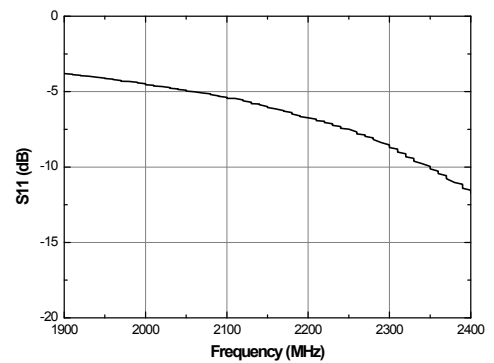
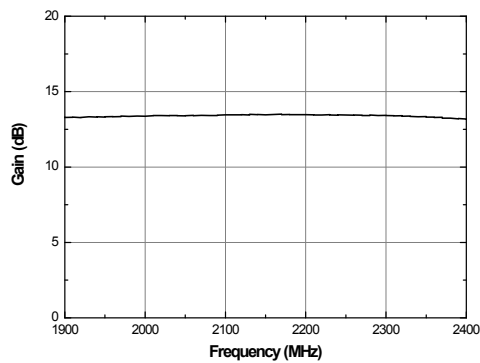
Schematic



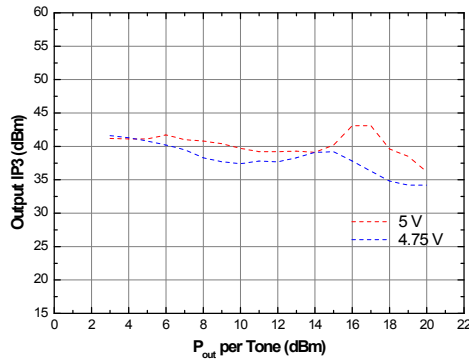
Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor (5V)

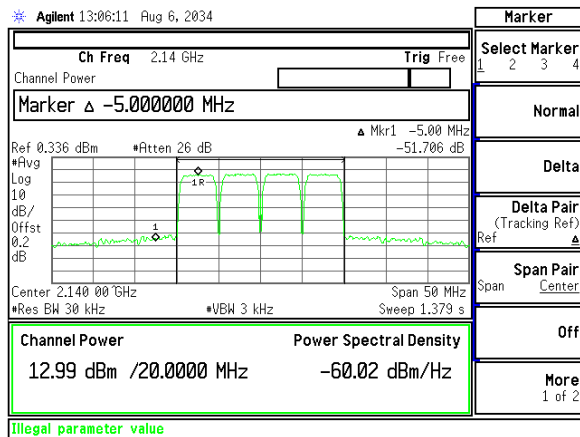


Output IP3 vs. Tone Power (Frequency = 2140 MHz)

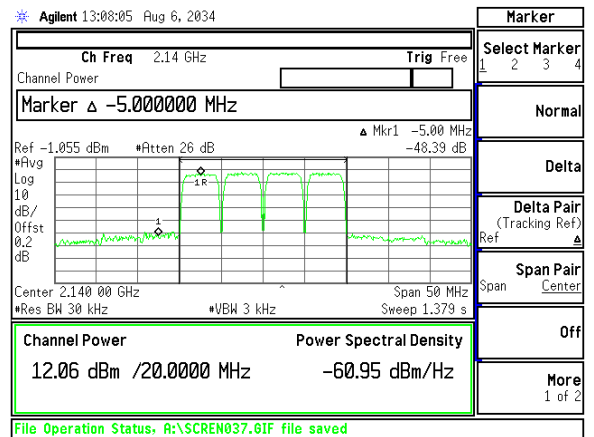


WCDMA ACLR

5V / 155mA



4.75V / 123mA



* Test Source : WCDMA 4FA(3GPP 3.4 12-00), Test Model1 w/64 DPCH, PAR=13dB @ 0.01 % probability on CCDF

APPLICATION CIRCUIT

WIMAX

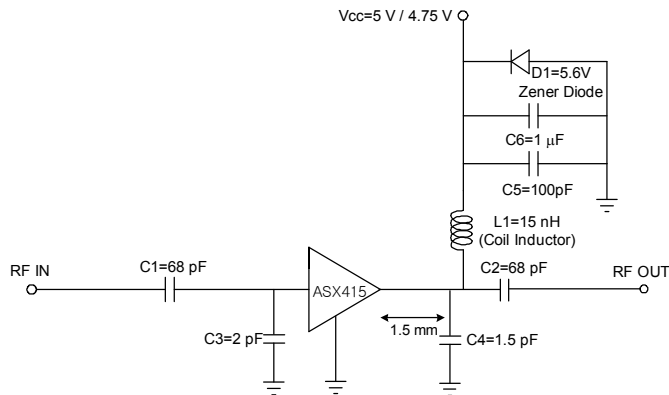
2500 ~ 2700

+5 V / 4.75V

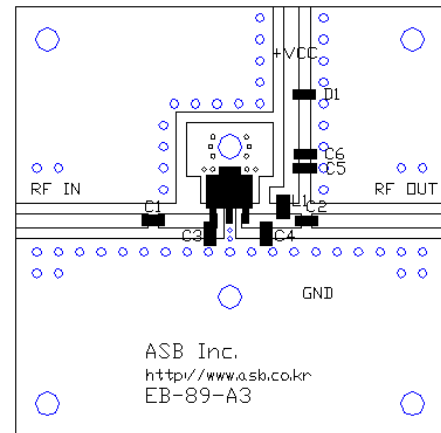
Frequency (MHz)	2500~2700	2500~2700
Magnitude S21 (dB)	11.5	11.5
Magnitude S11 (dB)	-7	-7
Magnitude S22 (dB)	-10	-10
Output P1dB (dBm)	29	28.5
Output IP3 ¹⁾ (dBm)	37	36
Noise Figure (dB)	4.2	3.9
Device Voltage (V)	5	4.75
Current (mA)	155	123

1) OIP3 is measured with two tones at an output power of +6 dBm/tone @ 5V & +4 dBm/tone @ 4.75V separated by 1MHz.

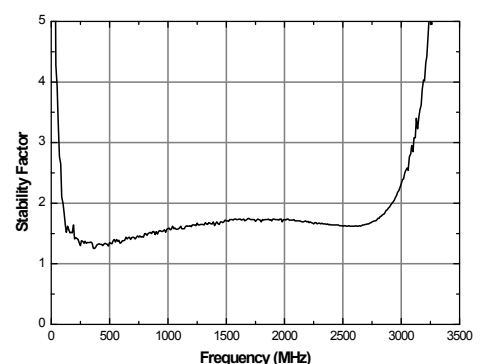
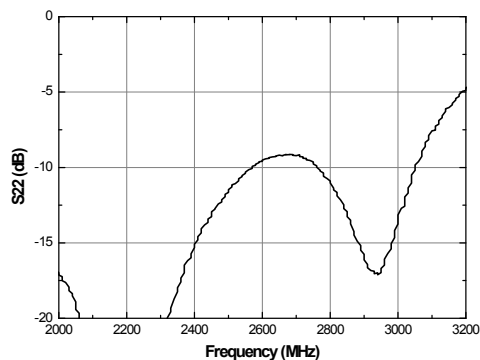
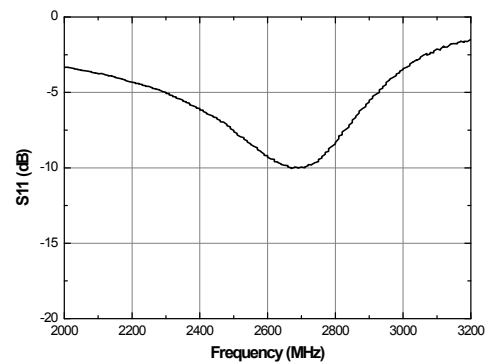
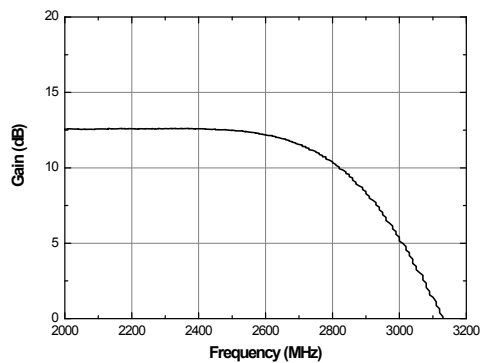
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)

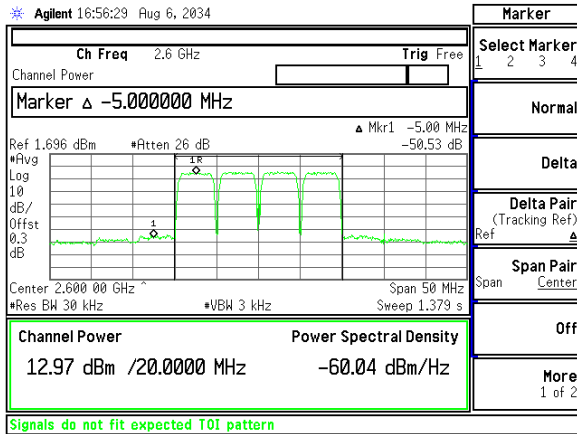


S-parameters & K-factor

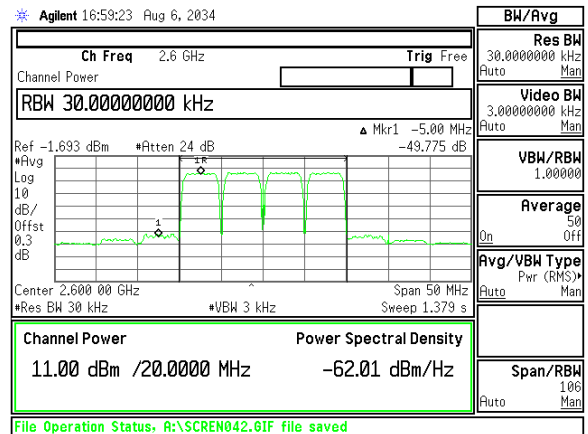


WCDMA ACLR

5V / 155mA



4.75V / 123mA



* Test Source : WCDMA 4FA(3GPP 3.4 12-00), Test Model1 w/64 DPCH, PAR=13dB @ 0.01 % probability on CCDF

APPLICATION CIRCUIT

WiMAX

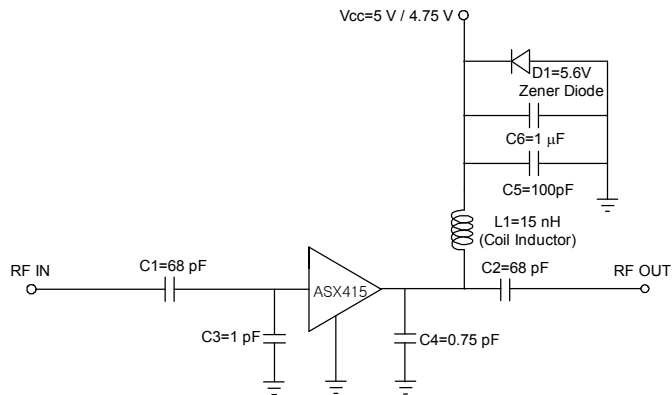
3500

+5 V / 4.75V

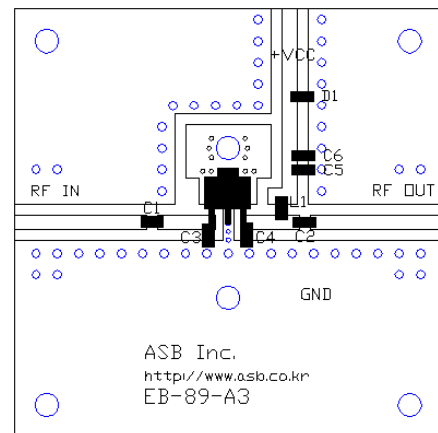
Frequency (MHz)	3500	3500
Magnitude S21 (dB)	9	9
Magnitude S11 (dB)	-7	-7
Magnitude S22 (dB)	-11	-11
Output P1dB (dBm)	25	24.5
Output IP3 ¹⁾ (dBm)	42	40
Noise Figure (dB)	5.4	4.8
Device Voltage (V)	5	4.75
Current (mA)	155	123

1) OIP3 is measured with two tones at an output power of +14 dBm/tone @ 5V & +13 dBm/tone @ 4.75V separated by 1MHz.

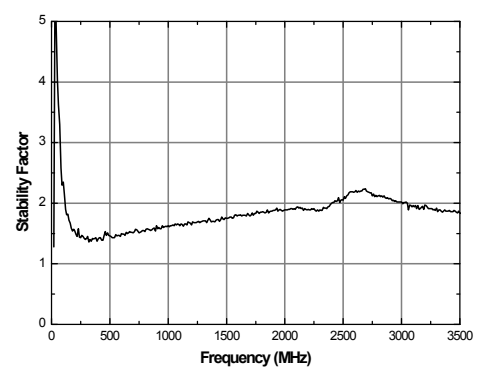
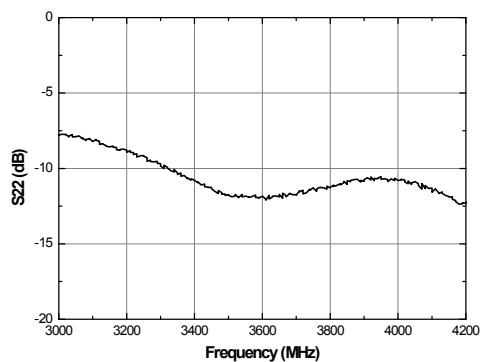
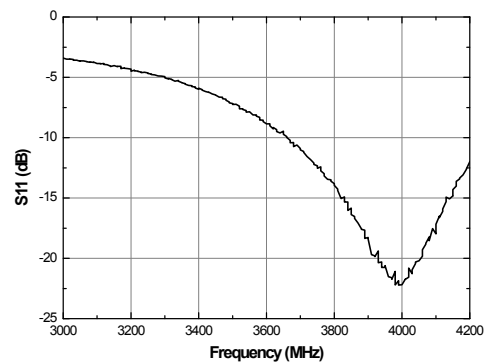
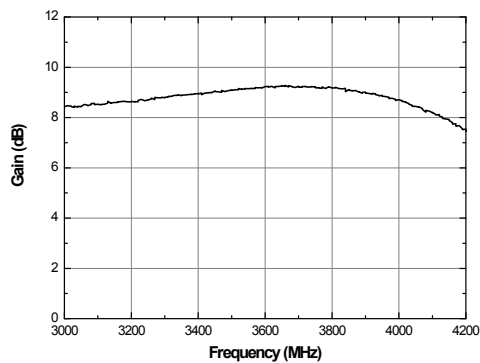
Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor



APPLICATION CIRCUIT

LTE

2300 ~ 2700

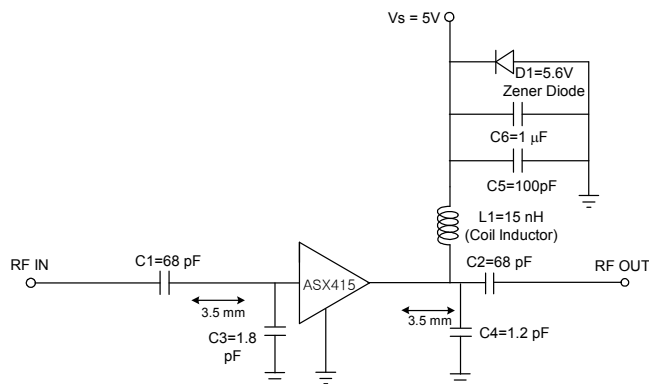
Gain Flatness < 0.5 dB

+5 V

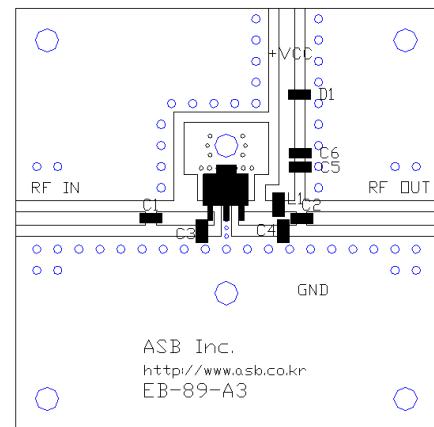
Frequency (MHz)	2300	2500	2700
Magnitude S21 (dB)	12.9	13.1	12.8
Magnitude S11 (dB)	-5	-8	-18
Magnitude S22 (dB)	-18	-18	-18
Output P1dB (dBm)	27.5		
Output IP3 ¹⁾ (dBm)	36		
Noise Figure (dB)	5.1		
Device Voltage (V)	5		
Current (mA)	155		

1) OIP3 is measured with two tones at an output power of +6 dBm/tone separated by 1 MHz.

Schematic



Board Layout (FR4, 40x40 mm², 0.8T)



S-parameters & K-factor

